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IIIV semiconductor nanowires for optoelectronic device applications

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#	Paper	IF	Citations
242	Transport properties of gallium nitride nanowire metal-oxide-semiconductor transistor. 2011 , 99, 1521	08	8
241	Monolithic integration of III-V nanowire with photonic crystal microcavity for vertical light emission. 2012 , 20, 7758-70		9
240	Analytical model of surface depletion in GaAs nanowires. 2012 , 112, 063705		44
239	Precursor flow rate manipulation for the controlled fabrication of twin-free GaAs nanowires on silicon substrates. <i>Nanotechnology</i> , 2012 , 23, 415702	3.4	10
238	Electrical properties of individual GaP nanowires doped by zinc. 2012 , 209, 2505-2509		6
237	Radial InP/InAsP quantum wells with high arsenic compositions on wurtzite-InP nanowires in the 1.3-µm region. 2012 ,		2
236	Direct measurement of surface states density and energy distribution in individual InAs nanowires. 2012 , 100, 262105		37
235	Growth and characterization of GaAs1 IkSbx nanowires. 2012,		
234	Ultralow surface recombination velocity in InP nanowires probed by terahertz spectroscopy. <i>Nano Letters</i> , 2012 , 12, 5325-30	11.5	127
233	Effect of a GaAsP shell on the optical properties of self-catalyzed GaAs nanowires grown on silicon. <i>Nano Letters</i> , 2012 , 12, 5269-74	11.5	28
232	Temperature-dependent terahertz conductivity of tin oxide nanowire films. <i>Journal Physics D:</i> Applied Physics, 2012 , 45, 465101	3	21
231	THE AB INITIO CALCULATION OF THE DYNAMICAL AND THE THERMODYNAMIC PROPERTIES OF THE ZINC-BLENDE GaX (X=N, P, As AND Sb). 2012 , 01, 1250026		1
230	Anisotropic photonic properties of III-V nanowires in the zinc-blende and wurtzite phase. <i>Nanoscale</i> , 2012 , 4, 1446-54	7.7	36
229	Self-catalyzed GaAsP nanowires grown on silicon substrates by solid-source molecular beam epitaxy. <i>Nano Letters</i> , 2013 , 13, 3897-902	11.5	61
228	Advances in semiconductor nanowire growth on graphene. 2013 , 7, 713-726		47
227	CdSe nanofiber and nanohorn structures on ITO substrates fabricated by electrochemical deposition. 2013 , 283, 982-985		6
226	Strengthening brittle semiconductor nanowires through stacking faults: insights from in situ mechanical testing. <i>Nano Letters</i> , 2013 , 13, 4369-73	11.5	42

225	Large-scale ordered 1D-nanomaterials arrays: Assembly or not?. 2013 , 8, 677-694		63
224	Composition-dependent ultra-high photoconductivity in ternary CdS x Se1⊠ nanobelts as measured by optical pump-terahertz probe spectroscopy. 2013 , 6, 808-821		21
223	Modeling InAs quantum-dot formation on the side surface of GaAs nanowires. 2013 , 39, 1047-1052		4
222	Illuminating the second conduction band and spin-orbit energy in single wurtzite InP nanowires. <i>Nano Letters</i> , 2013 , 13, 5367-72	11.5	21
221	Controlled modulation of diameter and composition along individual III-V nitride nanowires. <i>Nano Letters</i> , 2013 , 13, 331-6	11.5	63
220	Photoluminescence study of GaAs thin films and nanowires grown on Si(111). 2013 , 48, 1794-1798		16
219	Polarized Raman spectroscopy of corrugated MBE grown GaAs (6 3 1) homoepitaxial films. 2013 , 378, 105-108		1
218	Study of radial growth in patterned self-catalyzed GaAs nanowire arrays by gas source molecular beam epitaxy. 2013 , 7, 845-849		21
217	Attraction of semiconductor nanowires: An in situ observation. 2013, 61, 7166-7172		9
216	Three-dimensional in situ photocurrent mapping for nanowire photovoltaics. <i>Nano Letters</i> , 2013 , 13, 1405-9	11.5	34
215	Transient Photoconductivity of Ternary CdSSe Nanobelts As Measured by Time-Resolved Terahertz Spectroscopy. 2013 , 117, 12379-12384		17
214	Photoluminescence study of as-grown vertically standing wurtzite InP nanowire ensembles. <i>Nanotechnology</i> , 2013 , 24, 115706	3.4	12
213	Electronic properties of GaAs, InAs and InP nanowires studied by terahertz spectroscopy. <i>Nanotechnology</i> , 2013 , 24, 214006	3.4	205
212	Single InAs quantum dot grown at the junction of branched gold-free GaAs nanowire. <i>Nano Letters</i> , 2013 , 13, 1399-404	11.5	22
211	Excitonic properties of wurtzite InP nanowires grown on silicon substrate. <i>Nanotechnology</i> , 2013 , 24, 035704	3.4	22
210	Electrostatic model of radial pn junction nanowires. 2013 , 114, 074317		21
209	Unlocking doping and compositional profiles of nanowire ensembles using SIMS. <i>Nanotechnology</i> , 2013 , 24, 045701	3.4	16
208	Influence of Dephasing and Geometrical Parameters on Quantum Correction to DC Conductance of Cylindrical Nanowires. <i>Acta Physica Polonica A</i> , 2013 , 124, 838-840	0.6	

207	Measuring the electrical properties of semiconductor nanowires using terahertz conductivity spectroscopy. 2013 ,	
206	Probing the critical electronic properties of IIIIV nanowires using optical pump-terahertz probe spectroscopy. 2013 ,	
205	Structural and optical characterization of Mg-doped GaAs nanowires grown on GaAs and Si substrates. 2013 , 114, 183508	22
204	GaAs nanowires grown on Al-doped ZnO buffer layer. 2013 , 114, 084309	8
203	Surface depletion and electrical transport model of AlinP-passivated GaAs nanowires. 2013, 28, 105026	8
202	Study of growth of in situ Ga-catalyzed AlGaAs nanostructures using MOVPE technique. 2014 ,	
201	Position-controlled InP nanowires with 10᠒00 th pitches using Au-deposited SiO2/InP patterned substrates. 2014 , 104, 063102	16
200	Nanodevices: fabrication, prospects for low dimensional devices and applications. 2014 , 399-423	4
199	Vapor liquid solid-hydride vapor phase epitaxy (VLS-HVPE) growth of ultra-long defect-free GaAs nanowires: ab initio simulations supporting center nucleation. 2014 , 140, 194706	10
198	Comparison of Au and TiO2 based catalysts for the synthesis of chalcogenide nanowires. 2014 , 104, 253103	8
197	Enhanced efficiency of p-type doping by band-offset effect in wurtzite and zinc-blende GaAs/InAs-core-shell nanowires. 2014 , 116, 093704	1
196	Crystal facet effect on structural stability and electronic properties of wurtzite InP nanowires. 2014 , 115, 214301	6
195	Palladium assisted hetroepitaxial growth of an InAs nanowire by molecular beam epitaxy. 2014 , 29, 115005	3
194	GaAs/AlGaAs nanowire photodetector. <i>Nano Letters</i> , 2014 , 14, 2688-93	207
193	Engineering the Effective p-Type Dopant in GaAs/InAs CoreBhell Nanowires with Surface Dangling Bonds. 2014 , 118, 25209-25214	1
192	New insights into the temperature-dependent photoluminescence of Mg-doped GaAs nanowires and epilayers. 2014 , 2, 7104	13
191	Self-catalysed InAs 1-x Sb x nanowires grown directly on bare Si substrates. 2014 , 60, 572-575	17
190	Magnetoresistance anomalies resulting from Stark resonances in semiconductor nanowires with a constriction. 2014 , 26, 325301	7

189	Origin of strong photoluminescence polarization in GaNP nanowires. <i>Nano Letters</i> , 2014 , 14, 5264-9	11.5	17
188	Position-controlled uniform GaAs nanowires on silicon using nanoimprint lithography. <i>Nano Letters</i> , 2014 , 14, 960-6	11.5	117
187	Quantum confinement in Si and Ge nanostructures: Theory and experiment. <i>Applied Physics Reviews</i> , 2014 , 1, 011302	17.3	139
186	Electron mobilities approaching bulk limits in "surface-free" GaAs nanowires. <i>Nano Letters</i> , 2014 , 14, 5989-94	11.5	64
185	Wafer-scale fabrication of self-catalyzed 1.7 eV GaAsP core-shell nanowire photocathode on silicon substrates. <i>Nano Letters</i> , 2014 , 14, 2013-8	11.5	51
184	Self-catalyzed ternary core-shell GaAsP nanowire arrays grown on patterned Si substrates by molecular beam epitaxy. <i>Nano Letters</i> , 2014 , 14, 4542-7	11.5	37
183	Single step formation of indium and tin doped ZnO nanowires by thermal oxidation of indiumlinc and tin linc metal films: Growth and optical properties. 2014 , 40, 13611-13620		9
182	Engineering vertically aligned semiconductor nanowire arrays for applications in the life sciences. 2014 , 9, 172-196		108
181	Engineering of Bi2Se3nanowires by laser cutting. 2014 , 66, 10401		3
180	Mechanochemical synthesis of InAs nanocrystals. 2015 , 159, 474-477		6
179	Strain-induced band alignment in wurtzite/zinc-blende InAs heterostructured nanowires. 2015, 92,		9
178	Effects of loading misalignment and tapering angle on the measured mechanical properties of nanowires. <i>Nanotechnology</i> , 2015 , 26, 435704	3.4	6
177	Room-temperature electroluminescence from radial plb InP/InAsP/InP nanowire heterostructures in the 1.5-µm-wavelength region. 2015 , 54, 04DN02		7
176	Chemical vapor deposition of m-plane and c-plane InN nanowires on Si (100) substrate. 2015 , 415, 78-83		6
175	Nanospot soldering polystyrene nanoparticles with an optical fiber probe laser irradiating a metallic AFM probe based on the near-field enhancement effect. 2015 , 7, 2294-300		54
174	Modulation doping of GaAs/AlGaAs core-shell nanowires with effective defect passivation and high electron mobility. <i>Nano Letters</i> , 2015 , 15, 1336-42	11.5	69
173	. 2015 , 5, 854-864		28
172	Effects of Polytypism on Optical Properties and Band Structure of Individual Ga(N)P Nanowires from Correlative Spatially Resolved Structural and Optical Studies. <i>Nano Letters</i> , 2015 , 15, 4052-8	11.5	16

171	High Yield of GaAs Nanowire Arrays on Si Mediated by the Pinning and Contact Angle of Ga. <i>Nano Letters</i> , 2015 , 15, 2869-74	30
170	Bismuth catalyzed growth of GaAsBi nanowires by metalorganic vapor phase epitaxy. 2015 , 152, 298-301	13
169	Advanced IIIIV nanowire growth toward large-scale integration. 2015, 71-124	1
168	Optical characterisation of catalyst free GaAsP and GaAsP core-shell nanowires grown directly on Si substrates by MBE. 2015 ,	
167	Quantum confinement of excitons in wurtzite InP nanowires. 2015 , 117, 194306	17
166	Atomic-scale tomography of semiconductor nanowires. 2015 , 40, 896-909	7
165	IIIIV nanowires and nanowire optoelectronic devices. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 463001 ₃	91
164	Implications of the Differential Toxicological Effects of III-V Ionic and Particulate Materials for Hazard Assessment of Semiconductor Slurries. 2015 , 9, 12011-25	13
163	Single nanowire photoconductive terahertz detectors. <i>Nano Letters</i> , 2015 , 15, 206-10	78
162	Vapor-Liquid-Solid Growth of Semiconductor Nanowires. 2015 , 399-439	7
161	FIB patterning for position-controlled nanowire growth. 2016 , 640-641	
160	Polarized and spatially resolved Raman scattering from composition-graded wurtzite InGaAs nanowires. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 175105	5
159	Nanowire-based structures for infrared to ultraviolet emitters studied by cathodoluminescence. 2016 , 262, 134-41	5
158	VQS (vapor-quasiliquid-solid, vapor-quasisolid-solid) mechanism for the catalyst-free and catalyst-mediated non-eutectic syntheses of single-crystal nanowires. 2016 , 120, 084307	6
157	Determination of the stacking fault density in highly defective single GaAs nanowires by means of coherent diffraction imaging. 2016 , 18, 063021	10
156	Extracting the key electrical properties of semiconductors using optical pump terahertz probe spectroscopy. 2016 ,	
155	Characterization of quantum dot-like emission from GaAs/GaNAs core/shell nanowires. 2016,	
154	Doping concentration dependence of the photoluminescence spectra of n-type GaAs nanowires. 2016 , 108, 182106	33

153	Mechanical Behaviors of Semiconductor Nanowires. 2016 , 94, 109-158	4
152	Incorporation of Be dopant in GaAs core and core@hell nanowires by molecular beam epitaxy. 2016 , 34, 02L114	7
151	Polariton waveguides from a quantum dot chain in a photonic crystal waveguide: an architecture for waveguide quantum electrodynamics. 2016 , 3, 370	6
150	In Situ Heat-Induced Replacement of GaAs Nanowires by Au. <i>Nano Letters</i> , 2016 , 16, 3051-7 11.5	17
149	Impact of phonon scattering in Si/GaAs/InGaAs nanowires and FinFets: a NEGF perspective. 2016 , 15, 1130-1147	7
148	Selective Area Epitaxy of GaAs Microstructures by Close-Spaced Vapor Transport for Solar Energy Conversion Applications. 2016 , 1, 402-408	11
147	In situ electronic probing of semiconducting nanowires in an electron microscope. 2016 , 262, 183-8	3
146	Mobility-Modulation Field Effect Transistor Based on Electrospun Aluminum Doped Zinc Oxide Nanowires. 2016 , 5, Q92-Q97	9
145	Thermal Delocalization of Excitons in GaAs/AlGaAs Quantum Well Tube Nanowires. <i>Nano Letters</i> , 2016 , 16, 1392-7	6
144	Indium phosphide nanowires and their applications in optoelectronic devices. 2016 , 472, 20150804	17
143	Silver as Seed-Particle Material for GaAs NanowiresDictating Crystal Phase and Growth Direction by Substrate Orientation. <i>Nano Letters</i> , 2016 , 16, 2181-8	25
142	Effect of a High Density of Stacking Faults on the Youngß Modulus of GaAs Nanowires. <i>Nano</i> Letters, 2016 , 16, 1911-6	48
141	Increased Photoconductivity Lifetime in GaAs Nanowires by Controlled n-Type and p-Type Doping. 2016 , 10, 4219-27	51
140	Effects of Nitrogen Incorporation on Structural and Optical Properties of GaNAsP Nanowires. 2017 , 121, 7047-7055	9
139	Ecotoxicity assessment of ionic As(III), As(V), In(III) and Ga(III) species potentially released from novel III-V semiconductor materials. 2017 , 140, 30-36	14
138	Engineering the Size Distributions of Ordered GaAs Nanowires on Silicon. <i>Nano Letters</i> , 2017 , 17, 4101-4 1 0.8	34
137	Stability of rolled-up GaAs nanotubes. 2017 , 23, 204	3
136	Choice of Polymer Matrix for a Fast Switchable IIIIV Nanowire Terahertz Modulator. 2017 , 2, 1475-1480	1

135	Analytical modeling of the lattice and thermo-elastic coefficient mismatch-induced stress into silicon nanowires horizontally embedded on insulator-on-silicon substrates. <i>Superlattices and Microstructures</i> , 2017 , 101, 384-396	2.8	10
134	Dopant-Free Twinning Superlattice Formation in InSb and InP Nanowires. 2017 , 11, 1700310		12
133	Evaluating focused ion beam patterning for position-controlled nanowire growth using computer vision. 2017 , 902, 012020		2
132	Epitaxial Nanoflag Photonics: Semiconductor Nanoemitters Grown with Their Nanoantennas. <i>Nano Letters</i> , 2017 , 17, 6011-6017	11.5	6
131	Mechanical behaviors of nanowires. <i>Applied Physics Reviews</i> , 2017 , 4, 031104	17.3	39
130	X-ray pole figure analysis of catalyst free InAs nanowires on Si substrate. 2017 , 225, 108-114		4
129	Quantum plasmon model for the terahertz photoconductivity in intrinsic semiconductor nanowires. 2017 , 29, 415302		1
128	Impact of Rotational Twin Boundaries and Lattice Mismatch on III-V Nanowire Growth. 2017, 11, 8679-8	689	7
127	Large-Scale Statistics for Threshold Optimization of Optically Pumped Nanowire Lasers. <i>Nano Letters</i> , 2017 , 17, 4860-4865	11.5	23
126	Growth of Pure Zinc-Blende GaAs(P) Core-Shell Nanowires with Highly Regular Morphology. <i>Nano Letters</i> , 2017 , 17, 4946-4950	11.5	17
125	Effect of polytypism on the long and short range crystal structure of InAs nanostructures: An EXAFS and Raman spectroscopy study. 2017 , 35, 041803		
124	Scalable Nanowire Photonic Crystals: Molding the Light Emission of InGaN. <i>Advanced Functional Materials</i> , 2017 , 27, 1702364	15.6	33
123	Engineering the Photoresponse of InAs Nanowires. 2017 , 9, 43993-44000		34
122	Dynamics and control of gold-encapped gallium arsenide nanowires imaged by 4D electron microscopy. 2017 , 114, 12876-12881		12
121	Quantum Wells, Superlattices, and Band-Gap Engineering. 2017, 1-1		12
120	Facile growth of density- and diameter-controlled GaN nanobridges and their photodetector application. 2017 , 5, 11879-11884		17
119	Time-resolved photoluminescence characterization of GaAs nanowire arrays on native substrate. <i>Nanotechnology</i> , 2017 , 28, 505706	3.4	3
118	Electrical characterization of triple barrier GaAs/AlGaAs RTD with dependence of operating temperature and barrier lengths. 2017 , 58, 89-95		5

117	Gallium Arsenide nanowires for electrode application in solid oxide fuel cell grown using metal organic chemical vapor deposition. 2017 , 42, 9243-9251		1
116	THz modulators and detectors based on semiconductor nanowires. 2017,		
115	Substrate and Mg doping effects in GaAs nanowires. 2017 , 8, 2126-2138		4
114	Unexpected Au Alloying in Tailoring In-Doped SnTe Nanostructures with Gold Nanoparticles. 2017 , 7, 78		3
113	Field Emission from Self-Catalyzed GaAs Nanowires. 2017 , 7,		29
112	Graphene/Semiconductor Hybrid Heterostructures for Optoelectronic Device Applications. 2018 , 19, 41-83		124
111	Optimization and Characterization of Nanowires Semiconductor Based-Solar Cells. 2018, 409-417		
110	Sb Incorporation in Wurtzite and Zinc Blende InAs Sb Branches on InAs Template Nanowires. 2018 , 14, e1703785		4
109	Fluctuating potentials in GaAs:Si nanowires: critical reduction of the influence of polytypism on the electronic structure. <i>Nanoscale</i> , 2018 , 10, 3697-3708	7.7	12
108	In situ mechanical resonance behaviour of pristine and defective zinc blende GaAs nanowires. <i>Nanoscale</i> , 2018 , 10, 2588-2595	7.7	12
107	Excitonic terahertz photoconductivity in intrinsic semiconductor nanowires. 2018, 30, 235301		
106	Doping assessment in GaAs nanowires. <i>Nanotechnology</i> , 2018 , 29, 234001	3.4	30
105	Room-Temperature Mid-Infrared Emission from Faceted InAsSb Multi Quantum Wells Embedded in InAs Nanowires. <i>Nano Letters</i> , 2018 , 18, 235-240	11.5	9
104	Impact of N Incorporation on VLS Growth of GaP(N) Nanowires Utilizing UDMH. 2018 , 13, 417		6
103	Concurrent Zinc-Blende and Wurtzite Film Formation by Selection of Confined Growth Planes. <i>Nano Letters</i> , 2018 , 18, 7856-7862	11.5	19
102	Fabrication, Characterization and Parameter Extraction of InAs Nanowire-Based Device. 2018 , 31-51		
101	The effect of Sn addition on GaAs nanowire grown by vapor-liquid-solid growth mechanism. <i>Nanotechnology</i> , 2018 , 29, 465601	3.4	3
100	Materials characterization by synchrotron x-ray microprobes and nanoprobes. 2018 , 90,		61

99 Safety Concerns of Industrial Engineered Nanomaterials. **2018**, 1063-1072

98	Forbidden Band-Edge Excitons of Wurtzite-GaP: A Theoretical View. 2019 , 256, 1800238	10
97	Diameter and strain dependent structural, electronic and optical properties of gallium phosphide nanowires. 2019 ,	
96	Effect of Sn Addition on Epitaxial GaAs Nanowire Grown at Different Temperatures in Metal®rganic Chemical Vapor Deposition. 2019 , 19, 5314-5319	3
95	Increasing N content in GaNAsP nanowires suppresses the impact of polytypism on luminescence. <i>Nanotechnology</i> , 2019 , 30, 405703	3
94	In Situ Transmission Electron Microscopy Analysis of Copper-Germanium Nanowire Solid-State Reaction. <i>Nano Letters</i> , 2019 , 19, 8365-8371	5
93	III-V Nanowires and Related Nanostructures. 2019 , 217-239	
92	Band Structure of Wurtzite GaBiAs Nanowires. <i>Nano Letters</i> , 2019 , 19, 6454-6460	5
91	Understanding the Effect of Catalyst Size on the Epitaxial Growth of Hierarchical Structured InGaP Nanowires. <i>Nano Letters</i> , 2019 , 19, 8262-8269	3
90	Stacking defects in GaP nanowires: Electronic structure and optical properties. 2019 , 126, 084306	2
89	Four-Dimensional Probing of Phase-Reaction Dynamics in Au/GaAs Nanowires. <i>Nano Letters</i> , 2019 , 19, 781-786	3
88	Control of Conductivity of InGaAs Nanowires by Applied Tension and Surface States. <i>Nano Letters</i> , 2019 , 19, 4463-4469	11
87	Compositional Varied Core-Shell InGaP Nanowires Grown by Metal-Organic Chemical Vapor Deposition. <i>Nano Letters</i> , 2019 , 19, 3782-3788	13
86	Quantum Confinement Effect in the Absorption Spectra of Graphene Quantum Dots. 2019 , 4, 205-210	2
85	Gradients of Be-dopant concentration in self-catalyzed GaAs nanowires. <i>Nanotechnology</i> , 2019 , 30, 33579,9	4
84	Characterization of thermal transport and laser absorption properties of an individual pristine SWCNT. 2019 , 106, 9-14	
83	An insight into optical properties of Pb:CdS system (a theoretical study). 2019 , 6, 065904	6
82	In Situ Transmission Electron Microscopy Analysis of Aluminum-Germanium Nanowire Solid-State Reaction. <i>Nano Letters</i> , 2019 , 19, 2897-2904	; 29

(2020-2019)

81	Dilute nitrides-based nanowires-a promising platform for nanoscale photonics and energy technology. <i>Nanotechnology</i> , 2019 , 30, 292002	3.4	6
80	Ultra-fast photodetectors based on high-mobility indium gallium antimonide nanowires. 2019 , 10, 1664		39
79	Radial heterojunction based on single ZnO-CuO core-shell nanowire for photodetector applications. 2019 , 9, 5553		33
78	Recent advances in Sb-based III-V nanowires. <i>Nanotechnology</i> , 2019 , 30, 212002	3.4	5
77	Nanowires for High-Efficiency, Low-Cost Solar Photovoltaics. 2019 , 9, 87		27
76	Influence of Molecular Beam Epitaxy (MBE) Parameters on Catalyst-Free Growth of InAs Nanowires on Silicon (111) Substrate. 2019 , 48, 2174-2182		2
75	Growth of III☑ semiconductors and lasers on silicon substrates by MOCVD. 2019 , 229-282		5
74	Threshold reduction and yield improvement of semiconductor nanowire lasers via processing-related end-facet optimization. <i>Nanoscale Advances</i> , 2019 , 1, 4393-4397	5.1	5
73	Fabrication of star-shaped InP/GaInAs core-multishell nanowires by self-catalytic VLS mode. 2019 , 509, 66-70		1
72	Terahertz Spectroscopy of Nanomaterials: a Close Look at Charge-Carrier Transport. 2020 , 8, 1900623		18
71	Hydrogen evolution reaction electrocatalysis trends of confined gallium phosphide with substitutional defects. 2020 , 45, 23928-23936		5
70	High-quality epitaxial wurtzite structured InAs nanosheets grown in MBE. <i>Nanoscale</i> , 2020 , 12, 271-276	7.7	8
69	Effects of growth temperature and thermal annealing on optical quality of GaNAs nanowires emitting in the near-infrared spectral range. <i>Nanotechnology</i> , 2020 , 31, 065702	3.4	3
68	Exploring the Size Limitations of Wurtzite III-V Film Growth. <i>Nano Letters</i> , 2020 , 20, 686-693	11.5	13
67	Ion bombardment induced formation of self-organized wafer-scale GaInP nanopillar assemblies. 2020 , 38, 012801		1
66	Self-assembled nanodisks in coaxial GaAs/GaAsBi/GaAs core-multishell nanowires. <i>Nanoscale</i> , 2020 , 12, 20849-20858	7.7	1
65	Carbon Nanomaterials for Halide Perovskites-Based Hybrid Photodetectors. 2020 , 5, 2000643		6
64	III-V nanowire-based ultraviolet to terahertz photodetectors: Device strategies, recent developments, and future possibilities. 2020 , 130, 115989		4

63	Ink-Based Additive Nanomanufacturing of Functional Materials for Human-Integrated Smart Wearables. 2020 , 2, 2000117		9
62	Anodically Induced Chemical Etching of GaAs Wafers for a GaAs Nanowire-Based Flexible Terahertz Wave Emitter. 2020 , 12, 50703-50712		3
61	Highly Sensitive InSb Nanosheets Infrared Photodetector Passivated by Ferroelectric Polymer. <i>Advanced Functional Materials</i> , 2020 , 30, 2006156	15.6	15
60	In situ TEM observation of the vapor-solid-solid growth of InAs nanowires. <i>Nanoscale</i> , 2020 , 12, 11711-1	l 1,7,1 7	6
59	Probing dipole and quadrupole resonance mode in non-plasmonic nanowire using Raman spectroscopy. <i>Nanotechnology</i> , 2020 , 31, 425201	3.4	1
58	Nonlinear Charge Transport in InGaAs Nanowires at Terahertz Frequencies. <i>Nano Letters</i> , 2020 , 20, 322	5132331	6
57	Effects of Bi incorporation on recombination processes in wurtzite GaBiAs nanowires. <i>Nanotechnology</i> , 2020 , 31, 225706	3.4	1
56	Spin-polarized exciton formation in Co-doped GaN nanowires. 2020 , 245, 122756		4
55	Growth mechanism of helical EDy2S3 single crystals. 2021 , 23, 2196-2201		2
54	Formation of arsenic clusters in InAs nanowires with an AlO shell 2020 , 11, 177-182		
53	Monolithic Light Reflector-Nanowire Light Emitting Diodes. 2021 , 6, 2000885		2
52	Greener synthesis of nanocomposites and nanohybrids. 2021 , 389-404		1
51	Vertical growth characterization of InAs nanowires grown by selective area growth on patterned InP(1 1 1)B substrate by a MOCVD method. 2021 , 175, 107939		О
50	Photoic crystal nanobeam cavity devices for on-chip integrated silicon photonics. 2021 , 42, 023103		8
49	Measuring, controlling and exploiting heterogeneity in optoelectronic nanowires. 2021 , 3, 022004		3
49	Measuring, controlling and exploiting heterogeneity in optoelectronic nanowires. 2021 , 3, 022004 Efficient strain-induced light emission in lonsdaleite germanium. <i>Physical Review Materials</i> , 2021 , 5,	3.2	5
		3.2	

45	In-Cell Nanoelectronics: Opening the Door to Intracellular Electrophysiology. 2021 , 13, 127		10
44	The optical absorption of nanowires with hexagonal cross-sections. 2021 , 401, 127326		1
43	Effect of crystal structure on the Youngß modulus of GaP nanowires. Nanotechnology, 2021, 32,	3.4	1
42	passivation of GaInP nanowires using radial AlInP shells grown by MOVPE. <i>Nanotechnology</i> , 2021 , 32,	3.4	1
41	Various Applications of Nanowires. <i>Advances in Computer and Electrical Engineering Book Series</i> , 2021 , 17-53	0.3	1
40	Ultrafast high-capacity capture and release of uranium by a light-switchable nanotextured surface. <i>Nanoscale Advances</i> , 2021 , 3, 3615-3626	5.1	2
39	Integration Techniques for Micro/Nanostructure-based Large-Area Electronics. 2018,		12
38	Comparing Hall Effect and Field Effect Measurements on the Same Single Nanowire. <i>Nano Letters</i> , 2016 , 16, 205-11	11.5	31
37	Development of semiconducting ScN. <i>Physical Review Materials</i> , 2019 , 3,	3.2	27
36	Formation, electronic structure, and optical properties of self-assembled quantum-dot single-photon emitters in Ga(N,As,P) nanowires. <i>Physical Review Materials</i> , 2020 , 4,	3.2	3
35	Analytical description of nanowires. I. Regular cross sections for zincblende and diamond structures. <i>Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials</i> , 2019 , 75, 788-802	1.8	3
34	Electronic structure and optical properties of semiconductor nanowires polytypes. <i>European Physical Journal B</i> , 2020 , 93, 1	1.2	5
33	Self-induced thermo-optical effects in silicon and germanium dielectric nanoresonators. <i>Nanophotonics</i> , 2020 , 9, 3849-3861	6.3	11
32	Negative Photoconductive Effects in Uncooled InAs Nanowire Photodetectors. <i>Frontiers in Physics</i> , 2021 , 9,	3.9	O
31	Measuring the Energy Landscape in Single Semiconductor Nanowires. <i>Acta Physica Polonica A</i> , 2012 , 122, 316-320	0.6	
30	Silicon nanowire and nanohole arrays. Series in Materials Science and Engineering, 2017, 193-212		
29	Engineering III-V nanowires for optoelectronics: from epitaxy to terahertz photonics. 2018,		
28	Gallium vacanciesdommon non-radiative defects in ternary GaAsP and quaternary GaNAsP nanowires. <i>Nano Express</i> , 2020 , 1, 020022	2	О

27	Special Growth Techniques. <i>Graduate Texts in Physics</i> , 2020 , 469-520	0.3	
26	Depletion of Highly Abundant Protein Species from Biosamples by the Use of a Branched Silicon Nanopillar On-Chip Platform. <i>Analytical Chemistry</i> , 2021 , 93, 14527-14536	7.8	O
25	The application of one-dimensional nanostructures in terahertz frequency devices. <i>Applied Physics Reviews</i> , 2021 , 8, 041314	17.3	2
24	Optimal identification of Be-doped Al0.29Ga0.71As Schottky diode parameters using Dragonfly Algorithm: A thermal effect study. <i>Superlattices and Microstructures</i> , 2021 , 160, 107085	2.8	O
23	Topical Review: Pathways toward cost-effective single-junction III-V solar cells. <i>Journal Physics D:</i> Applied Physics,	3	3
22	Strain Engineering of Undoped and Na-Doped 1D Cd 8O 8 Nanowires. SSRN Electronic Journal,	1	
21	InSb Nanowire Direct Growth on Plastic for Monolithic Flexible Device Fabrication. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 539-545	4	1
20	Nanomaterials for Quantum Information Science and Engineering Advanced Materials, 2022, e2109621	24	6
19	Lattice dynamics of GeSn alloy nanowires Nanoscale, 2022,	7.7	
18	Twins and grain boundaries-dominated the reverse Bauschinger effect and tension-compression asymmetry. <i>Journal of Materials Research and Technology</i> , 2022 , 18, 15-28	5.5	2
17	Direct GaAs Nanowire Growth and Monolithic Light-Emitting Diode Fabrication on Flexible Plastic Substrates. <i>Advanced Photonics Research</i> , 2100311	1.9	1
16	Scalable Platform for Nanocrystal-Based Quantum Electronics. <i>Advanced Functional Materials</i> , 2112941	15.6	O
15	A Study on the Effects of Gallium Droplet Consumption and Post Growth Annealing on Te-Doped GaAs Nanowire Properties Grown by Self-Catalyzed Molecular Beam Epitaxy. <i>Catalysts</i> , 2022 , 12, 451	4	O
14	Templated electrodeposition as a scalable and surfactant-free approach to the synthesis of Au nanoparticles with tunable aspect ratios. <i>Nanoscale Advances</i> ,	5.1	1
13	Investigation of Quantum and Dielectric Confinement based Dopant Deactivation in the Extension Region of FinFET. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	
12	2D Manganese Nanosheets with Optical-Limiting Behavior for Precision Instrument and Eye Protection. <i>ACS Applied Nano Materials</i> , 2022 , 5, 8080-8088	5.6	1
11	Analytic description of nanowires II: morphing of regular cross sections for zincblende- and diamond-structures to match arbitrary shapes. <i>Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials</i> , 2022 , 78,	1.8	O
10	Bandgap engineering and modulation of thermodynamic, and optical properties of III-N monolayers XN (X = In, Ga & amp; Al) by mutual alloying. 2022 , 97, 095806		

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 $9\,$ $\,$ In-situ off-axis electron holography of real-time dopant diffusion in GaAs nanowires.

8	Polarization Anisotropy in Nanowires: Fundamental Concepts and Progress Towards Terahertz-Band Polarization Devices. 2022 , 100417	0
7	Attenuation of the Bauschinger effect and enhancement of tensionBompression asymmetry in single crystal aluminum by temperature. 2022 , 12, 21235-21246	0
6	GaAs/GaP superlattice nanowires: growth, vibrational and optical properties.	O
5	Strain engineering of undoped and Na-doped 1D Cd8O8 nanowires. 2022, 76,	0
4	Nanowires for UVIIisIR Optoelectronic Synaptic Devices. 2208807	2
3	Optical and Electrical Properties of Low-Dimensional Crystalline Materials: A Review. 2023 , 13, 108	О
2	Photoactive materials and devices for energy-efficient soft wearable optoelectronic systems. 2023 , 110, 108379	Ο
1	Structural Engineering in a Microscale Laser Diode with InGaN Tunnel-Junction Nanorods.	О